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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	168MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	72
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	192K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 13x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	90-UFBGA, WLCSP
Supplier Device Package	90-WLCSP (4.22x3.97)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f405ogy6vtr

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2 Description

The STM32F405xx and STM32F407xx family is based on the high-performance ARM® Cortex®-M4 32-bit RISC core operating at a frequency of up to 168 MHz. The Cortex-M4 core features a Floating point unit (FPU) single precision which supports all ARM single-precision data-processing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) which enhances application security.

The STM32F405xx and STM32F407xx family incorporates high-speed embedded memories (Flash memory up to 1 Mbyte, up to 192 Kbytes of SRAM), up to 4 Kbytes of backup SRAM, and an extensive range of enhanced I/Os and peripherals connected to two APB buses, three AHB buses and a 32-bit multi-AHB bus matrix.

All devices offer three 12-bit ADCs, two DACs, a low-power RTC, twelve general-purpose 16-bit timers including two PWM timers for motor control, two general-purpose 32-bit timers, a true random number generator (RNG). They also feature standard and advanced communication interfaces.

- Up to three I²Cs
- Three SPIs, two I²Ss full duplex. To achieve audio class accuracy, the I2S peripherals can be clocked via a dedicated internal audio PLL or via an external clock to allow synchronization.
- Four USARTs plus two UARTs
- An USB OTG full-speed and a USB OTG high-speed with full-speed capability (with the ULPI),
- Two CANs
- An SDIO/MMC interface
- Ethernet and the camera interface available on STM32F407xx devices only.

New advanced peripherals include an SDIO, an enhanced flexible static memory control (FSMC) interface (for devices offered in packages of 100 pins and more), a camera interface for CMOS sensors. Refer to [Table 2: STM32F405xx and STM32F407xx: features and peripheral counts](#) for the list of peripherals available on each part number.

The STM32F405xx and STM32F407xx family operates in the –40 to +105 °C temperature range from a 1.8 to 3.6 V power supply. The supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor: refer to [Section : Internal reset OFF](#). A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F405xx and STM32F407xx family offers devices in various packages ranging from 64 pins to 176 pins. The set of included peripherals changes with the device chosen.

These features make the STM32F405xx and STM32F407xx microcontroller family suitable for a wide range of applications:

- Motor drive and application control
- Medical equipment
- Industrial applications: PLC, inverters, circuit breakers
- Printers, and scanners
- Alarm systems, video intercom, and HVAC
- Home audio appliances

clock entry is available when necessary (for example if an indirectly used external oscillator fails).

Several prescalers allow the configuration of the three AHB buses, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the three AHB buses is 168 MHz while the maximum frequency of the high-speed APB domains is 84 MHz. The maximum allowed frequency of the low-speed APB domain is 42 MHz.

The devices embed a dedicated PLL (PLL12S) which allows to achieve audio class performance. In this case, the I²S master clock can generate all standard sampling frequencies from 8 kHz to 192 kHz.

2.2.13 Boot modes

At startup, boot pins are used to select one out of three boot options:

- Boot from user Flash
- Boot from system memory
- Boot from embedded SRAM

The boot loader is located in system memory. It is used to reprogram the Flash memory by using USART1 (PA9/PA10), USART3 (PC10/PC11 or PB10/PB11), CAN2 (PB5/PB13), USB OTG FS in Device mode (PA11/PA12) through DFU (device firmware upgrade).

2.2.14 Power supply schemes

- $V_{DD} = 1.8$ to 3.6 V: external power supply for I/Os and the internal regulator (when enabled), provided externally through V_{DD} pins.
- V_{SSA} , $V_{DDA} = 1.8$ to 3.6 V: external analog power supplies for ADC, DAC, Reset blocks, RCs and PLL. V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS} , respectively.
- $V_{BAT} = 1.65$ to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

Refer to [Figure 21: Power supply scheme](#) for more details.

Note: V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to [Section : Internal reset OFF](#)).

Refer to [Table 2](#) in order to identify the packages supporting this option.

2.2.15 Power supply supervisor

Internal reset ON

On packages embedding the PDR_ON pin, the power supply supervisor is enabled by holding PDR_ON high. On all other packages, the power supply supervisor is always enabled.

The device has an integrated power-on reset (POR) / power-down reset (PDR) circuitry coupled with a Brownout reset (BOR) circuitry. At power-on, POR/PDR is always active and ensures proper operation starting from 1.8 V. After the 1.8 V POR threshold level is reached, the option byte loading process starts, either to confirm or modify default BOR threshold levels, or to disable BOR permanently. Three BOR thresholds are available through option bytes. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for an external reset circuit.

Two external ceramic capacitors should be connected on V_{CAP_1} & V_{CAP_2} pin. Refer to [Figure 21: Power supply scheme](#) and [Figure 16: VCAP_1/VCAP_2 operating conditions](#).

All packages have regulator ON feature.

Regulator OFF

This feature is available only on packages featuring the BYPASS_REG pin. The regulator is disabled by holding BYPASS_REG high. The regulator OFF mode allows to supply externally a V_{12} voltage source through V_{CAP_1} and V_{CAP_2} pins.

Since the internal voltage scaling is not managed internally, the external voltage value must be aligned with the targeted maximum frequency. Refer to [Table 14: General operating conditions](#).

The two 2.2 μF ceramic capacitors should be replaced by two 100 nF decoupling capacitors.

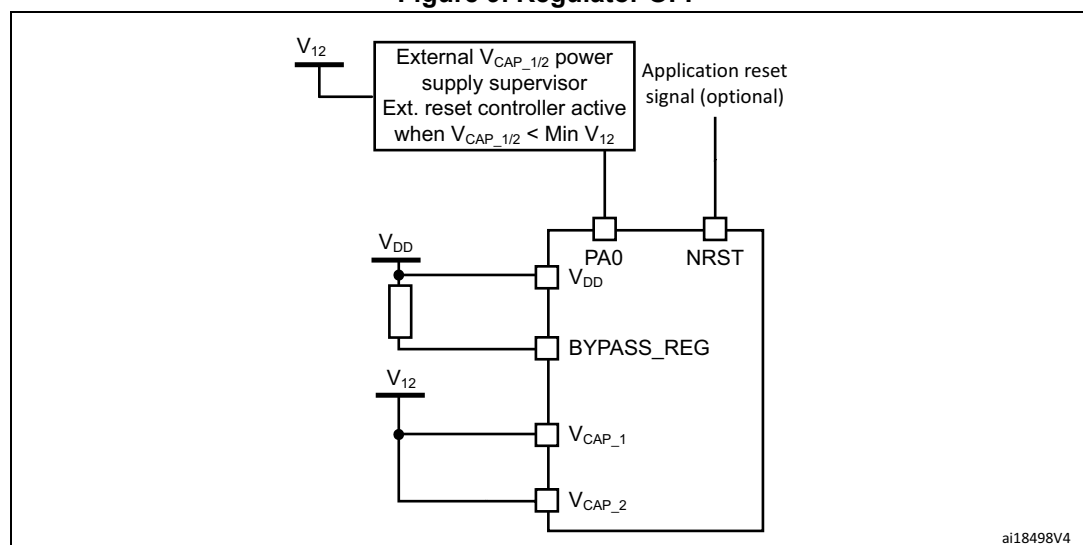
Refer to [Figure 21: Power supply scheme](#)

When the regulator is OFF, there is no more internal monitoring on V_{12} . An external power supply supervisor should be used to monitor the V_{12} of the logic power domain. PA0 pin should be used for this purpose, and act as power-on reset on V_{12} power domain.

In regulator OFF mode the following features are no more supported:

- PA0 cannot be used as a GPIO pin since it allows to reset a part of the V_{12} logic power domain which is not reset by the NRST pin.
- As long as PA0 is kept low, the debug mode cannot be used under power-on reset. As a consequence, PA0 and NRST pins must be managed separately if the debug connection under reset or pre-reset is required.
- The standby mode is not available

Figure 9. Regulator OFF



Eight DAC trigger inputs are used in the device. The DAC channels are triggered through the timer update outputs that are also connected to different DMA streams.

2.2.38 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

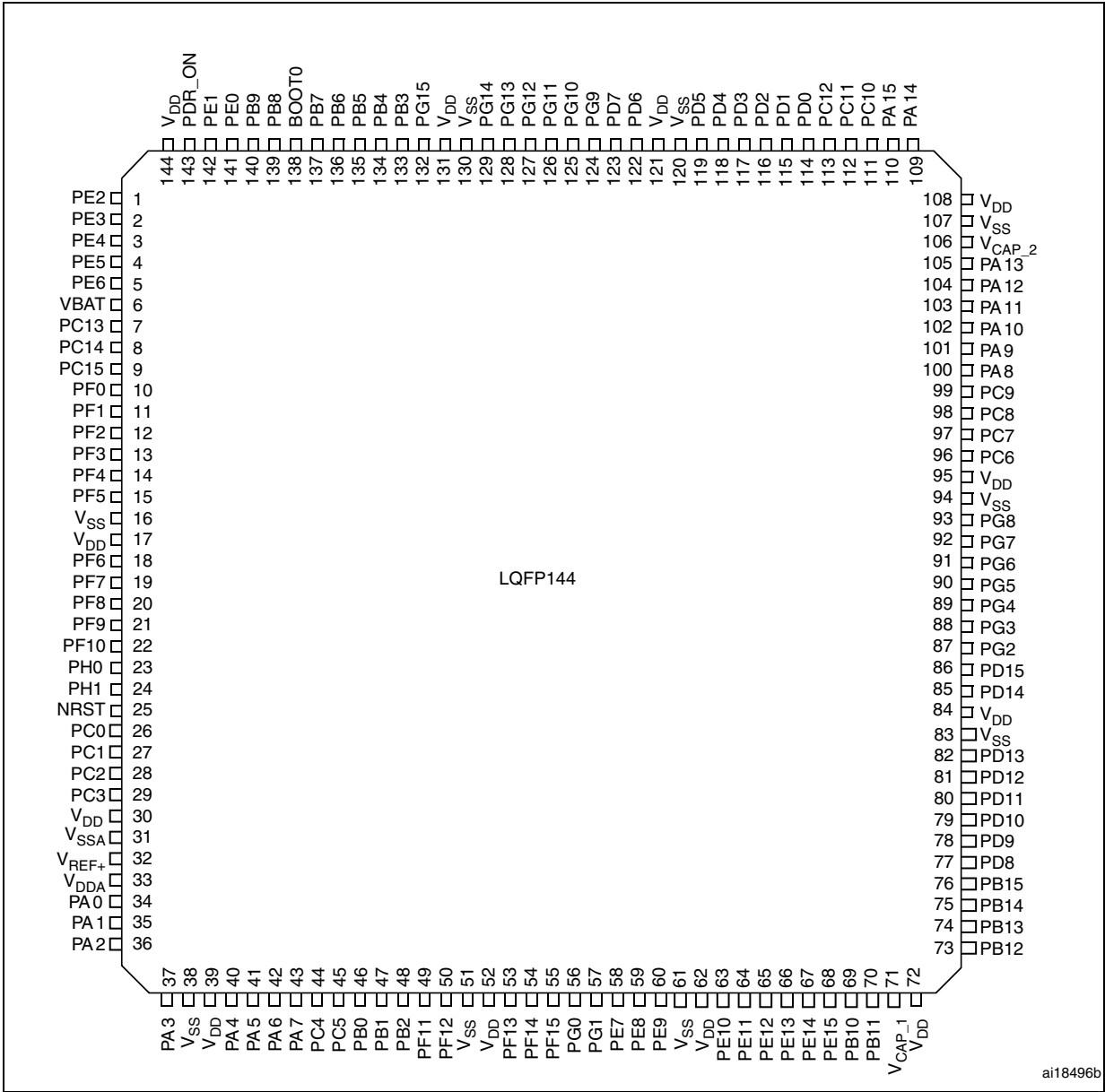
Debug is performed using 2 pins only instead of 5 required by the JTAG (JTAG pins could be re-use as GPIO with alternate function): the JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

2.2.39 Embedded Trace Macrocell™

The ARM Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F40xxx through a small number of ETM pins to an external hardware trace port analyser (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer that runs the debugger software. TPA hardware is commercially available from common development tool vendors.

The Embedded Trace Macrocell operates with third party debugger software tools.

Figure 14. STM32F40xxx LQFP144 pinout



1. The above figure shows the package top view.

Table 7. STM32F40xxx pin and ball definitions (continued)

Pin number						Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176						
-	-	-	11	H3	17	PF1	I/O	FT	-	FSMC_A1 / I2C2_SCL / EVENTOUT	-
-	-	-	12	H2	18	PF2	I/O	FT	-	FSMC_A2 / I2C2_SMBA / EVENTOUT	-
-	-	-	13	J2	19	PF3	I/O	FT	(4)	FSMC_A3/EVENTOUT	ADC3_IN9
-	-	-	14	J3	20	PF4	I/O	FT	(4)	FSMC_A4/EVENTOUT	ADC3_IN14
-	-	-	15	K3	21	PF5	I/O	FT	(4)	FSMC_A5/EVENTOUT	ADC3_IN15
-	C9	10	16	G2	22	V _{SS}	S	-	-	-	-
-	B8	11	17	G3	23	V _{DD}	S	-	-	-	-
-	-	-	18	K2	24	PF6	I/O	FT	(4)	TIM10_CH1 / FSMC_NIORD/ EVENTOUT	ADC3_IN4
-	-	-	19	K1	25	PF7	I/O	FT	(4)	TIM11_CH1/FSMC_NREG/ EVENTOUT	ADC3_IN5
-	-	-	20	L3	26	PF8	I/O	FT	(4)	TIM13_CH1 / FSMC_NIOWR/ EVENTOUT	ADC3_IN6
-	-	-	21	L2	27	PF9	I/O	FT	(4)	TIM14_CH1 / FSMC_CD/ EVENTOUT	ADC3_IN7
-	-	-	22	L1	28	PF10	I/O	FT	(4)	FSMC_INTR/ EVENTOUT	ADC3_IN8
5	F10	12	23	G1	29	PH0/OSC_IN (PH0)	I/O	FT	-	EVENTOUT	OSC_IN ⁽⁴⁾
6	F9	13	24	H1	30	PH1/OSC_OUT (PH1)	I/O	FT	-	EVENTOUT	OSC_OUT ⁽⁴⁾
7	G10	14	25	J1	31	NRST	I/O	RST	-	-	-
8	E10	15	26	M2	32	PC0	I/O	FT	(4)	OTG_HS_ULPI_STP/ EVENTOUT	ADC123_IN10
9	-	16	27	M3	33	PC1	I/O	FT	(4)	ETH_MDC/ EVENTOUT	ADC123_IN11
10	D10	17	28	M4	34	PC2	I/O	FT	(4)	SPI2_MISO / OTG_HS_ULPI_DIR / ETH_MII_TXD2 /I2S2ext_SD/ EVENTOUT	ADC123_IN12

Table 9. Alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/2/3	SPI1/SPI2/I2S2/I2S2ext	SPI3/I2Sext/I2S3	USART1/2/3/I2S3ext	UART4/5/USART6	CAN1/2/TIM12/13/14	OTG_FS/OTG_HS	ETH	FSMC/SDIO/OTG_FS	DCMI		
Port B	PB0	-	TIM1_CH2N	TIM3_CH3	TIM8_CH2N	-	-	-	-	-	-	OTG_HS_ULPI_D1	ETH_MII_RXD2	-	-	-	EVENTOUT
	PB1	-	TIM1_CH3N	TIM3_CH4	TIM8_CH3N	-	-	-	-	-	-	OTG_HS_ULPI_D2	ETH_MII_RXD3	-	-	-	EVENTOUT
	PB2	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PB3	JTDO/TRACES WO	TIM2_CH2	-	-	-	SPI1_SCK	SPI3_SCK I2S3_CK	-	-	-	-	-	-	-	-	EVENTOUT
	PB4	NJTRST	-	TIM3_CH1	-	-	SPI1_MISO	SPI3_MISO	I2S3ext_SD	-	-	-	-	-	-	-	EVENTOUT
	PB5	-	-	TIM3_CH2	-	I2C1_SMB_A	SPI1_MOSI	SPI3_MOSI I2S3_SD	-	-	CAN2_RX	OTG_HS_ULPI_D7	ETH_PPS_OUT	-	DCMI_D10	-	EVENTOUT
	PB6	-	-	TIM4_CH1	-	I2C1_SCL	-	-	USART1_TX	-	CAN2_TX	-	-	-	DCMI_D5	-	EVENTOUT
	PB7	-	-	TIM4_CH2	-	I2C1_SDA	-	-	USART1_RX	-	-	-	-	FSMC_NL	DCMI_VSYN_C	-	EVENTOUT
	PB8	-	-	TIM4_CH3	TIM10_CH1	I2C1_SCL	-	-	-	-	CAN1_RX	-	ETH_MII_TXD3	SDIO_D4	DCMI_D6	-	EVENTOUT
	PB9	-	-	TIM4_CH4	TIM11_CH1	I2C1_SDA	SPI2_NSS I2S2_WS	-	-	-	CAN1_TX	-	-	SDIO_D5	DCMI_D7	-	EVENTOUT
	PB10	-	TIM2_CH3	-	-	I2C2_SCL	SPI2_SCK I2S2_CK	-	USART3_TX	-	-	OTG_HS_ULPI_D3	ETH_MII_RX_ER	-	-	-	EVENTOUT
	PB11	-	TIM2_CH4	-	-	I2C2_SDA	-	-	USART3_RX	-	-	OTG_HS_ULPI_D4	ETH_MII_TX_EN ETH_RMII_TX_EN	-	-	-	EVENTOUT
	PB12	-	TIM1_BKIN	-	-	I2C2_SMBA	SPI2_NSS I2S2_WS	-	USART3_CK	-	CAN2_RX	OTG_HS_ULPI_D5	ETH_MII_TXD0 ETH_RMII_TXD0	OTG_HS_ID	-	-	EVENTOUT
	PB13	-	TIM1_CH1N	-	-	-	SPI2_SCK I2S2_CK	-	USART3_CTS	-	CAN2_TX	OTG_HS_ULPI_D6	ETH_MII_TXD1 ETH_RMII_TXD1	-	-	-	EVENTOUT
	PB14	-	TIM1_CH2N	-	TIM8_CH2N	-	SPI2_MISO	I2S2ext_SD	USART3_RTS	-	TIM12_CH1	-	-	OTG_HS_DM	-	-	EVENTOUT
	PB15	RTC_REFIN	TIM1_CH3N	-	TIM8_CH3N	-	SPI2_MOSI I2S2_SD	-	-	-	TIM12_CH2	-	-	OTG_HS_DP	-	-	EVENTOUT

Table 23. Typical and maximum current consumptions in Stop mode

Symbol	Parameter	Conditions	Typ	Max				Unit
			T _A = 25 °C	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C		
I _{DD_STOP}	Supply current in Stop mode with main regulator in Run mode	Flash in Stop mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.45	1.5	11.00	20.00	mA	
		Flash in Deep power-down mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.40	1.5	11.00	20.00		
	Supply current in Stop mode with main regulator in Low-power mode	Flash in Stop mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.31	1.1	8.00	15.00		
		Flash in Deep power-down mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.28	1.1	8.00	15.00		

Table 24. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions	Typ			Max ⁽¹⁾		Unit
			T _A = 25 °C			T _A = 85 °C	T _A = 105 °C	
			V _{DD} = 1.8 V	V _{DD} = 2.4 V	V _{DD} = 3.3 V	V _{DD} = 3.6 V		
I _{DD_STBY}	Supply current in Standby mode	Backup SRAM ON, low-speed oscillator and RTC ON	3.0	3.4	4.0	20	36	μA
		Backup SRAM OFF, low-speed oscillator and RTC ON	2.4	2.7	3.3	16	32	
		Backup SRAM ON, RTC OFF	2.4	2.6	3.0	12.5	24.8	
		Backup SRAM OFF, RTC OFF	1.7	1.9	2.2	9.8	19.2	

1. Guaranteed by characterization.

A device reset allows normal operations to be resumed.

The test results are given in [Table 43](#). They are based on the EMS levels and classes defined in application note AN1709.

Table 43. EMS characteristics

Symbol	Parameter	Conditions	Level/Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP176, $T_A = +25\text{ }^{\circ}\text{C}$, $f_{HCLK} = 168\text{ MHz}$, conforms to IEC 61000-4-2	2B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	$V_{DD} = 3.3\text{ V}$, LQFP176, $T_A = +25\text{ }^{\circ}\text{C}$, $f_{HCLK} = 168\text{ MHz}$, conforms to IEC 61000-4-2	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Static latchup

Two complementary static tests are required on six parts to assess the latchup performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latchup standard.

Table 46. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105\text{ }^{\circ}\text{C}$ conforming to JESD78A	II level A

5.3.15 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of $5\text{ }\mu\text{A}/+0\text{ }\mu\text{A}$ range), or other functional failure (for example reset, oscillator frequency deviation).

Negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.

The test results are given in [Table 47](#).

Table 50. I/O AC characteristics⁽¹⁾⁽²⁾ (continued)

OSPEEDRy [1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Typ	Max	Unit
11	$F_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 30 \text{ pF}, V_{DD} > 2.70 \text{ V}$	-	-	100 ⁽⁴⁾	MHz
			$C_L = 30 \text{ pF}, V_{DD} > 1.8 \text{ V}$	-	-	50 ⁽⁴⁾	
			$C_L = 10 \text{ pF}, V_{DD} > 2.70 \text{ V}$	-	-	180 ⁽⁴⁾	
			$C_L = 10 \text{ pF}, V_{DD} > 1.8 \text{ V}$	-	-	100 ⁽⁴⁾	
	$t_{f(\text{IO})\text{out}}/$ $t_{r(\text{IO})\text{out}}$	Output high to low level fall time and output low to high level rise time	$C_L = 30 \text{ pF}, V_{DD} > 2.70 \text{ V}$	-	-	4	ns
			$C_L = 30 \text{ pF}, V_{DD} > 1.8 \text{ V}$	-	-	6	
			$C_L = 10 \text{ pF}, V_{DD} > 2.70 \text{ V}$	-	-	2.5	
			$C_L = 10 \text{ pF}, V_{DD} > 1.8 \text{ V}$	-	-	4	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller		10	-	-	ns

1. Guaranteed by characterization.
2. The I/O speed is configured using the OSPEEDRy[1:0] bits. Refer to the STM32F4xx reference manual for a description of the GPIOx_SPEEDR GPIO port output speed register.
3. The maximum frequency is defined in [Figure 37](#).
4. For maximum frequencies above 50 MHz, the compensation cell should be used.

Figure 37. I/O AC characteristics definition

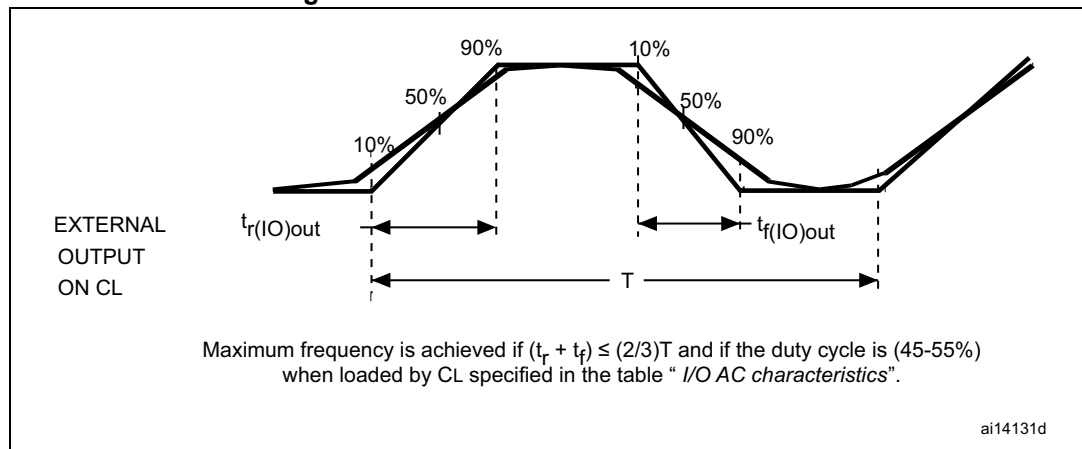
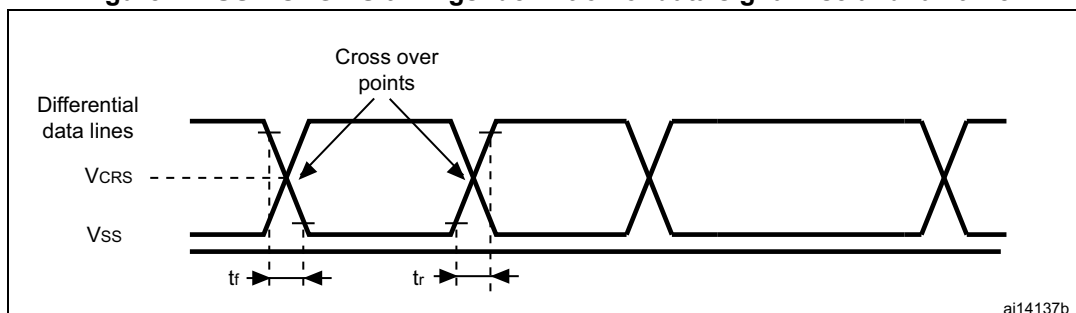


Figure 44. USB OTG FS timings: definition of data signal rise and fall time

Table 59. USB OTG FS electrical characteristics⁽¹⁾

Driver characteristics					
Symbol	Parameter	Conditions	Min	Max	Unit
t_r	Rise time ⁽²⁾	$C_L = 50 \text{ pF}$	4	20	ns
t_f	Fall time ⁽²⁾	$C_L = 50 \text{ pF}$	4	20	ns
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage	-	1.3	2.0	V

1. Guaranteed by design.

2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

USB HS characteristics

Unless otherwise specified, the parameters given in [Table 62](#) for ULPI are derived from tests performed under the ambient temperature, f_{HCLK} frequency summarized in [Table 61](#) and V_{DD} supply voltage conditions summarized in [Table 60](#), with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load $C = 30 \text{ pF}$
- Measurement points are done at CMOS levels: $0.5V_{DD}$.

Refer to Section [Section 5.3.16: I/O port characteristics](#) for more details on the input/output characteristics.

Table 60. USB HS DC electrical characteristics

Symbol	Parameter	Min. ⁽¹⁾	Max. ⁽¹⁾	Unit
Input level	V_{DD} USB OTG HS operating voltage	2.7	3.6	V

1. All the voltages are measured from the local ground potential.

Table 61. USB HS clock timing parameters⁽¹⁾

Parameter	Symbol	Min	Nominal	Max	Unit
f_{HCLK} value to guarantee proper operation of USB HS interface	-	30	-	-	MHz
Frequency (first transition)	8-bit $\pm 10\%$ F_{START_8BIT}	54	60	66	MHz

Table 61. USB HS clock timing parameters⁽¹⁾

Parameter		Symbol	Min	Nominal	Max	Unit
Frequency (steady state) ± 500 ppm		F_{STEADY}	59.97	60	60.03	MHz
Duty cycle (first transition)	8-bit $\pm 10\%$	$D_{\text{START_8BIT}}$	40	50	60	%
Duty cycle (steady state) ± 500 ppm		D_{STEADY}	49.975	50	50.025	%
Time to reach the steady state frequency and duty cycle after the first transition		T_{STEADY}	-	-	1.4	ms
Clock startup time after the de-assertion of SuspendM	Peripheral	$T_{\text{START_DEV}}$	-	-	5.6	ms
	Host	$T_{\text{START_HOST}}$	-	-	-	
PHY preparation time after the first transition of the input clock		T_{PREP}	-	-	-	μs

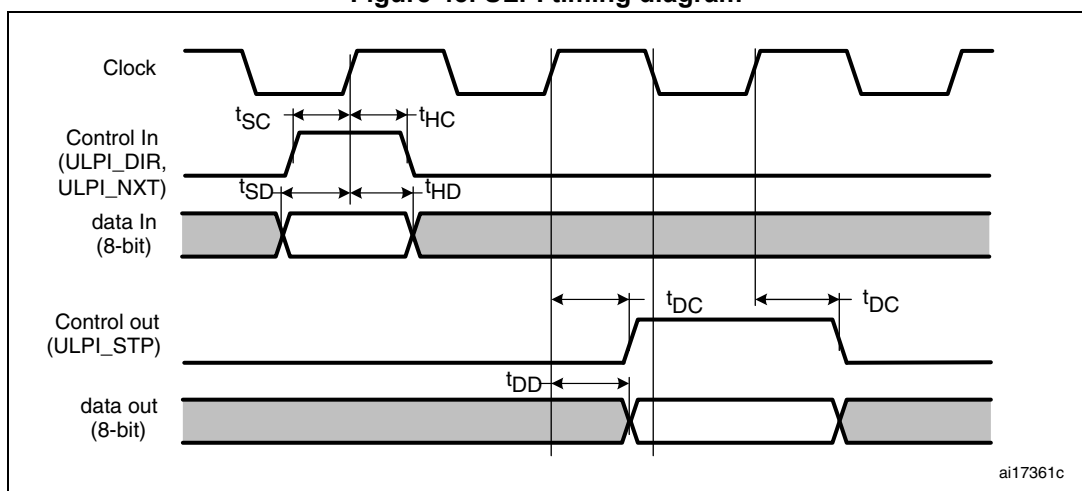
1. Guaranteed by design.

Table 62. ULPI timing

Parameter	Symbol	Value ⁽¹⁾		Unit
		Min.	Max.	
Control in (ULPI_DIR) setup time	t_{SC}	-	2.0	ns
Control in (ULPI_NXT) setup time		-	1.5	
Control in (ULPI_DIR, ULPI_NXT) hold time	t_{HC}	0	-	
Data in setup time	t_{SD}	-	2.0	
Data in hold time	t_{HD}	0	-	
Control out (ULPI_STP) setup time and hold time	t_{DC}	-	9.2	
Data out available from clock rising edge	t_{DD}	-	10.7	

1. $V_{\text{DD}} = 2.7 \text{ V}$ to 3.6 V and $T_{\text{A}} = -40$ to $85 \text{ }^{\circ}\text{C}$.

Figure 45. ULPI timing diagram



Ethernet characteristics

Unless otherwise specified, the parameters given in [Table 64](#), [Table 65](#) and [Table 66](#) for SMI, RMII and MII are derived from tests performed under the ambient temperature, f_{HCLK} frequency summarized in [Table 14](#) and VDD supply voltage conditions summarized in [Table 63](#), with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$.

Refer to [Section 5.3.16: I/O port characteristics](#) for more details on the input/output characteristics.

Table 63. Ethernet DC electrical characteristics

Symbol		Parameter	Min. ⁽¹⁾	Max. ⁽¹⁾	Unit
Input level	V _{DD}	Ethernet operating voltage	2.7	3.6	V

1. All the voltages are measured from the local ground potential.

[Table 64](#) gives the list of Ethernet MAC signals for the SMI (station management interface) and [Figure 46](#) shows the corresponding timing diagram.

Figure 46. Ethernet SMI timing diagram

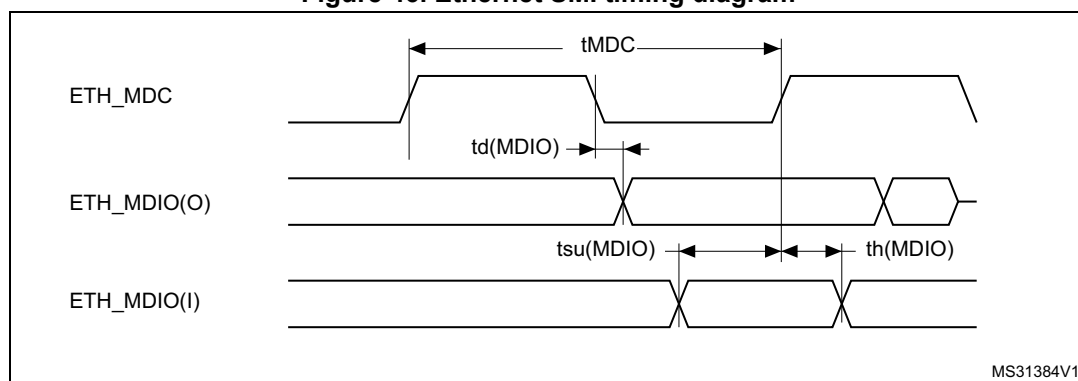


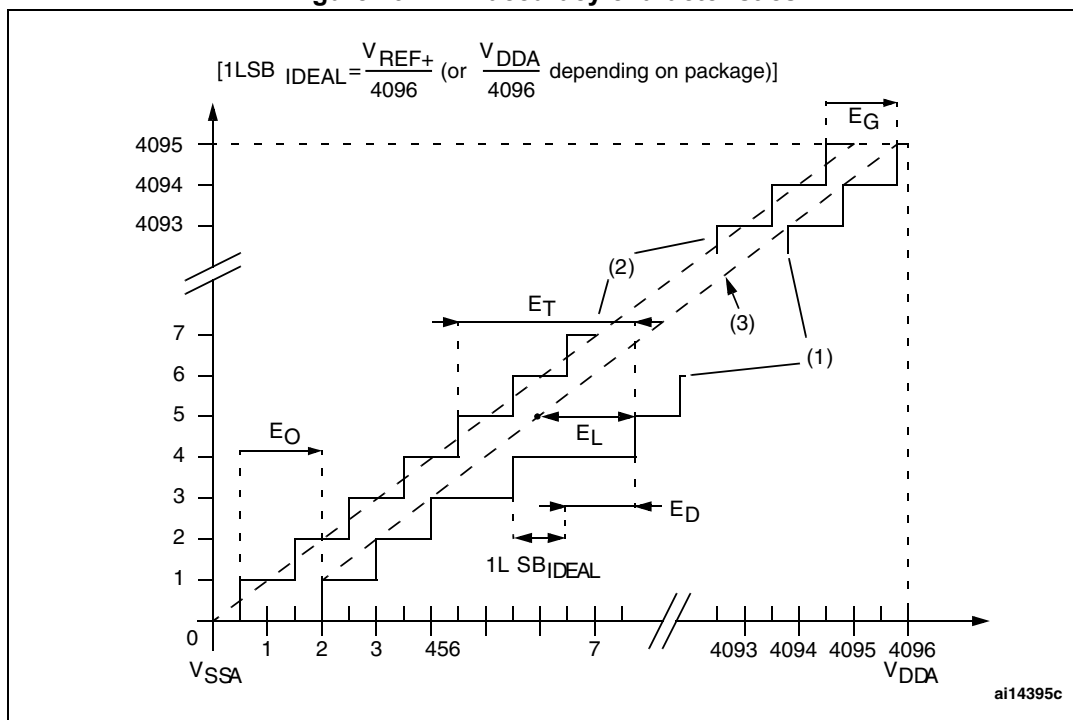
Table 64. Dynamic characteristics: Eternity MAC signals for SMI⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
t_{MDC}	MDC cycle time(2.38 MHz)	411	420	425	ns
$T_d(MDIO)$	Write data valid time	6	10	13	
$t_{su}(MDIO)$	Read data setup time	12	-	-	
$t_h(MDIO)$	Read data hold time	0	-	-	

1. Guaranteed by characterization.

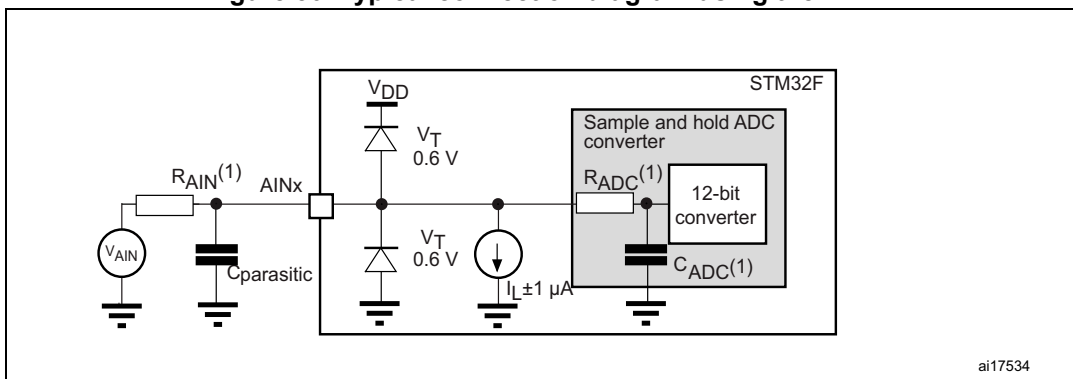
[Table 65](#) gives the list of Ethernet MAC signals for the RMII and [Figure 47](#) shows the corresponding timing diagram.

Figure 49. ADC accuracy characteristics



1. See also [Table 68](#).
2. Example of an actual transfer curve.
3. Ideal transfer curve.
4. End point correlation line.
5. E_T = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves.
 E_O = Offset Error: deviation between the first actual transition and the first ideal one.
 E_G = Gain Error: deviation between the last ideal transition and the last actual one.
 E_D = Differential Linearity Error: maximum deviation between actual steps and the ideal one.
 E_L = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

Figure 50. Typical connection diagram using the ADC



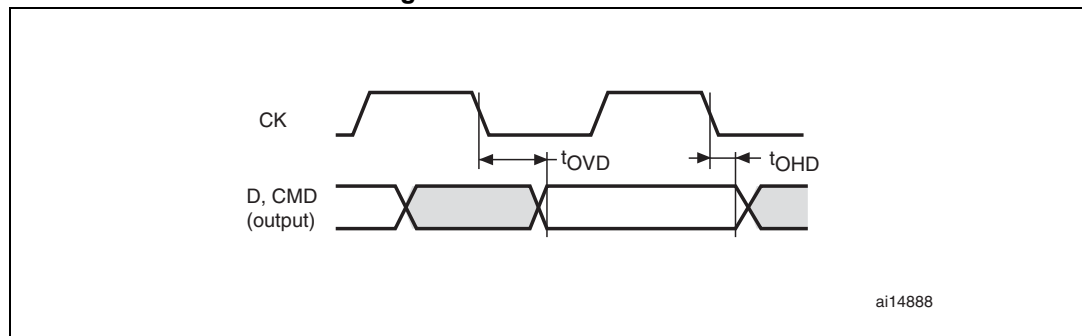
1. Refer to [Table 67](#) for the values of R_{AIN} , R_{ADC} and C_{ADC} .
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 5 pF). A high $C_{parasitic}$ value downgrades conversion accuracy. To remedy this, f_{ADC} should be reduced.

Table 74. DAC characteristics (continued)

Symbol	Parameter	Min	Typ	Max	Unit	Comments
Offset ⁽⁴⁾	Offset error (difference between measured value at Code (0x800) and the ideal value = $V_{REF+}/2$)	-	-	±10	mV	Given for the DAC in 12-bit configuration
		-	-	±3	LSB	Given for the DAC in 10-bit at $V_{REF+} = 3.6$ V
		-	-	±12	LSB	Given for the DAC in 12-bit at $V_{REF+} = 3.6$ V
Gain error ⁽⁴⁾	Gain error	-	-	±0.5	%	Given for the DAC in 12-bit configuration
$t_{SETTLING}^{(4)}$	Settling time (full scale: for a 10-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±4LSB)	-	3	6	µs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
THD ⁽⁴⁾	Total Harmonic Distortion Buffer ON	-	-	-	dB	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
Update rate ⁽²⁾	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	1	MS/s	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
$t_{WAKEUP}^{(4)}$	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	6.5	10	µs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ input code between lowest and highest possible ones.
PSRR+ ⁽²⁾	Power supply rejection ratio (to V_{DDA}) (static DC measurement)	-	-67	-40	dB	No R_{LOAD} , $C_{LOAD} = 50$ pF

1. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to [Section : Internal reset OFF](#)).
2. Guaranteed by design.
3. The quiescent mode corresponds to a state where the DAC maintains a stable output level to ensure that no dynamic consumption occurs.
4. Guaranteed by characterization.

Figure 74. SD default mode

Table 88. Dynamic characteristics: SD / MMC characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f _{PP}	Clock frequency in data transfer mode		0		48	MHz
	SDIO_CK/f _{PCLK2} frequency ratio		-	-	8/3	-
t _{W(CKL)}	Clock low time	f _{PP} = 48 MHz	8.5	9	-	ns
t _{W(CKH)}	Clock high time	f _{PP} = 48 MHz	8.3	10	-	
CMD, D inputs (referenced to CK) in MMC and SD HS mode						
t _{ISU}	Input setup time HS	f _{PP} = 48 MHz	3	-	-	ns
t _{IH}	Input hold time HS	f _{PP} = 48 MHz	0	-	-	
CMD, D outputs (referenced to CK) in MMC and SD HS mode						
t _{OV}	Output valid time HS	f _{PP} = 48 MHz	-	4.5	6	ns
t _{OH}	Output hold time HS	f _{PP} = 48 MHz	1	-	-	
CMD, D inputs (referenced to CK) in SD default mode						
t _{ISUD}	Input setup time SD	f _{PP} = 24 MHz	1.5	-	-	ns
t _{IHD}	Input hold time SD	f _{PP} = 24 MHz	0.5	-	-	
CMD, D outputs (referenced to CK) in SD default mode						
t _{OVD}	Output valid default time SD	f _{PP} = 24 MHz	-	4.5	7	ns
t _{OHD}	Output hold default time SD	f _{PP} = 24 MHz	0.5	-	-	

1. Guaranteed by characterization.

5.3.29 RTC characteristics

Table 89. RTC characteristics

Symbol	Parameter	Conditions	Min	Max
-	f_{PCLK1} /RTCCLK frequency ratio	Any read/write operation from/to an RTC register	4	-

7 Part numbering

Table 99. Ordering information scheme

Example:	STM32	F	405	R	E	T	6	xxx
Device family								
STM32 = ARM-based 32-bit microcontroller								
Product type								
F = general-purpose								
Device subfamily								
405 = STM32F40xxx, connectivity								
407 = STM32F40xxx, connectivity, camera interface, Ethernet								
Pin count								
R = 64 pins								
O = 90 pins								
V = 100 pins								
Z = 144 pins								
I = 176 pins								
Flash memory size								
E = 512 Kbytes of Flash memory								
G = 1024 Kbytes of Flash memory								
Package								
T = LQFP								
H = UFBGA								
Y = WLCSP								
Temperature range								
6 = Industrial temperature range, –40 to 85 °C.								
7 = Industrial temperature range, –40 to 105 °C.								
Options								
xxx = programmed parts								
TR = tape and reel								

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.